
2SC5480

Silicon NPN Triple Diffused
Horizontal Deflection Output

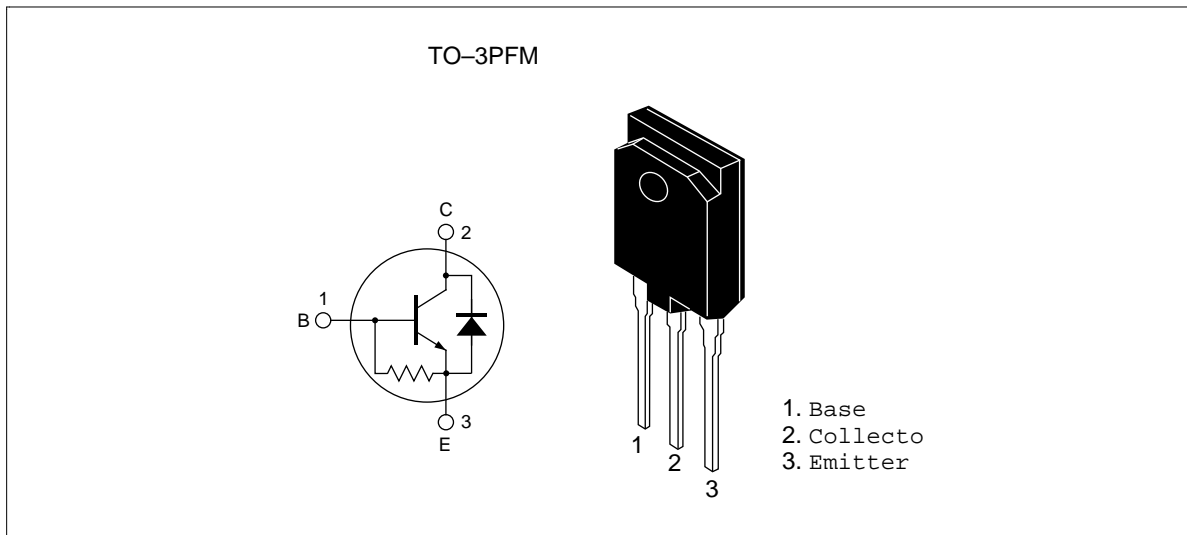
HITACHI

ADE-208-632 (Z)
1st. Edition
Oct. 1, 1998

Features

- High breakdown voltage
 $V_{CES} = 1500 \text{ V}$
- Isolated package
TO-3PFM
- Built-in damper diode

Outline



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Absolute Maximum Ratings (Ta = 25°C)

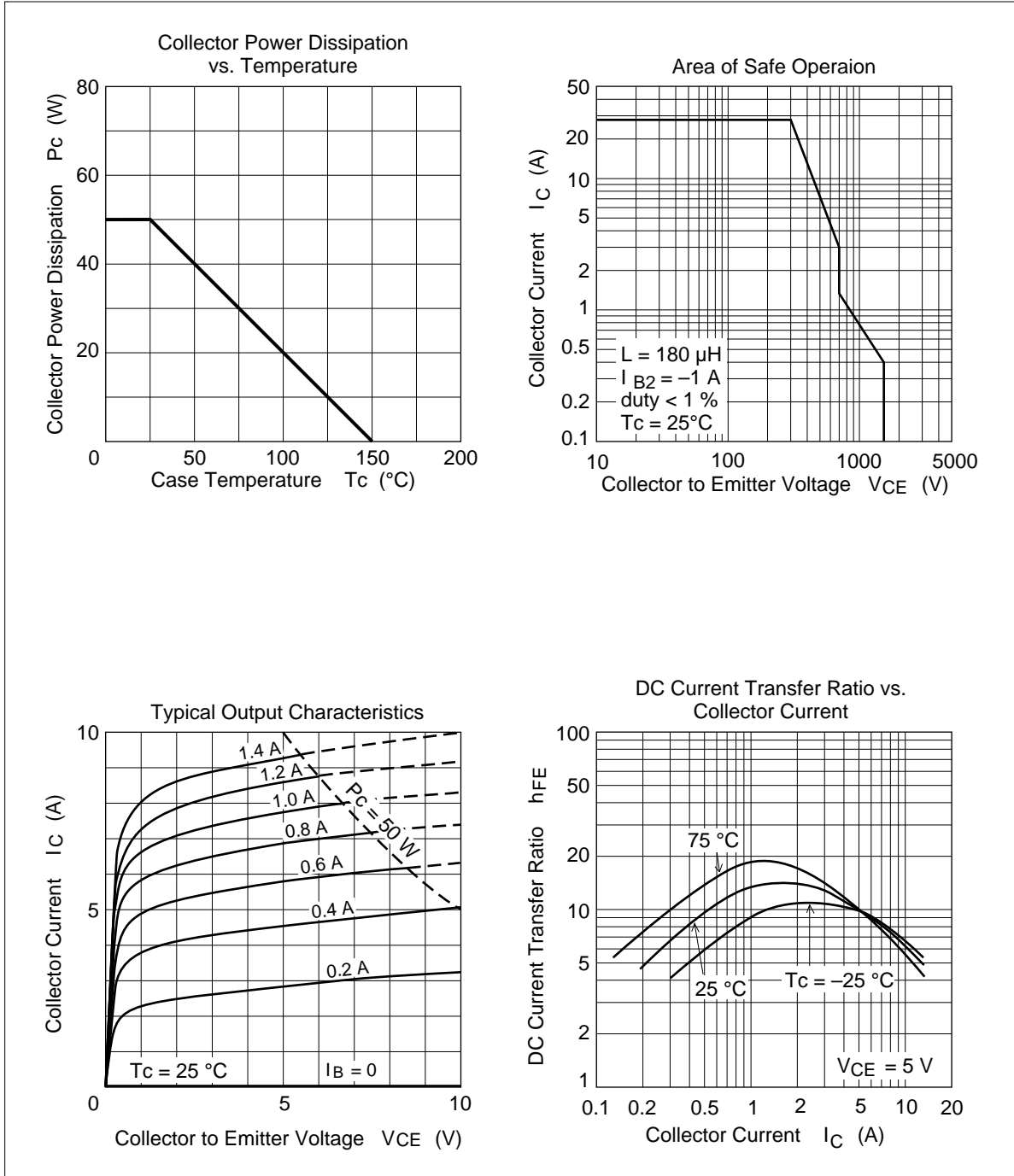
Item	Symbol	Ratings	Unit
Collector to emitter voltage	V_{CES}	1500	V
Emitter to base voltage	V_{EBO}	5	V
Collector current	I_C	14	A
Collector peak current	$i_{c(peak)}$	28	A
Collector power dissipation	P_C ^{Note1}	50	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C
Collector to emitter diode forward current	I_D	14	A

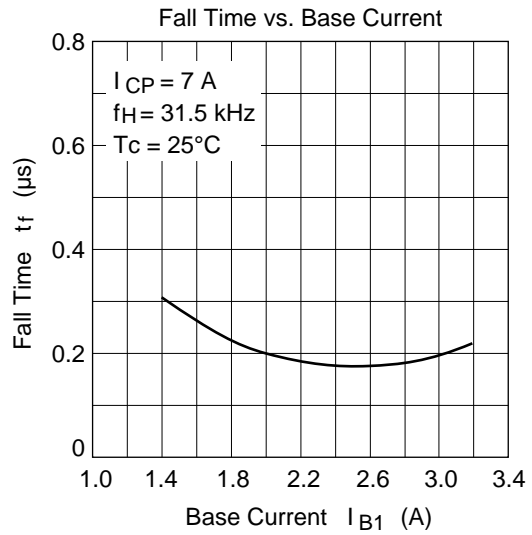
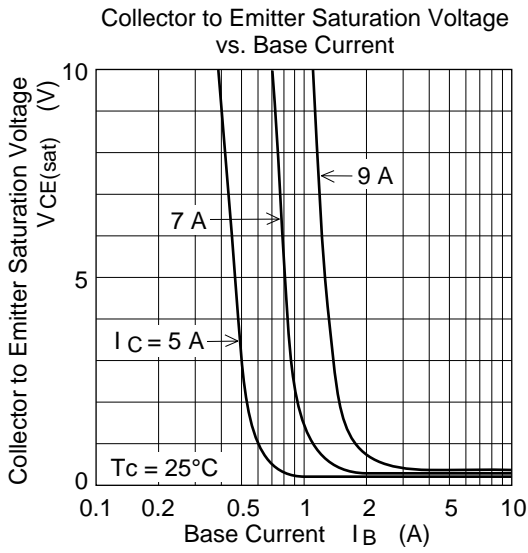
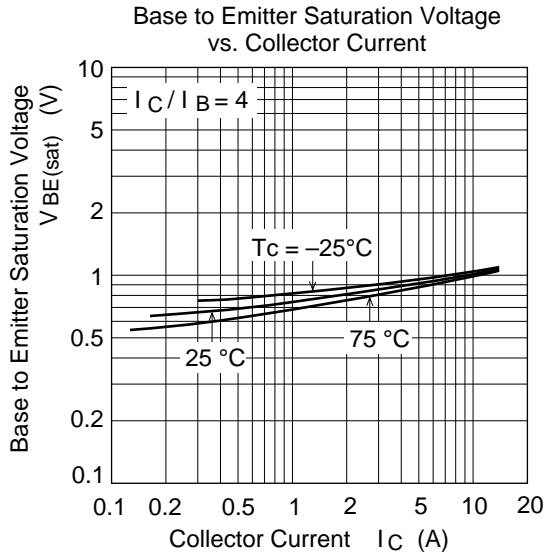
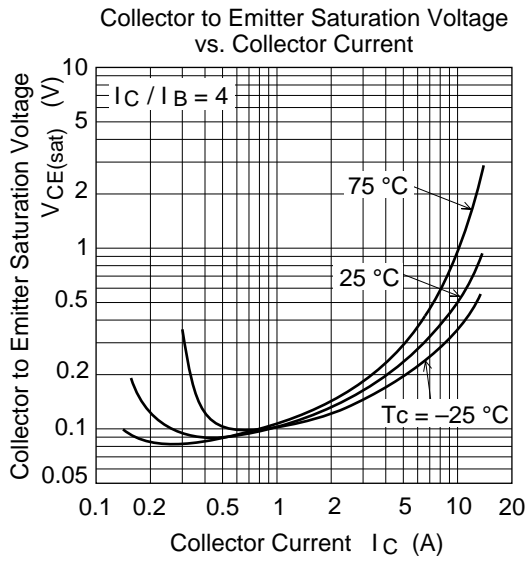
Note: 1. Value at $T_C = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	—	—	V	$I_E = 500\text{mA}$, $I_C = 0$
Collector cutoff current	I_{CES}	—	—	500	μA	$V_{CE} = 1500\text{V}$, $R_{BE} = 0$
DC current transfer ratio	h_{FE1}	5	—	25		$V_{CE} = 5\text{V}$, $I_C = 1\text{A}$
DC current transfer ratio	h_{FE2}	4	—	7		$V_{CE} = 5\text{V}$, $I_C = 10\text{A}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	5	V	$I_C = 10\text{A}$, $I_B = 2.5\text{A}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C = 10\text{A}$, $I_B = 2.5\text{A}$
Collector to emitter diode forward voltage	V_{ECF}	—	—	2	V	$I_F = 14\text{A}$
Fall time	t_f	—	0.2	0.4	μs	$I_{CP} = 7\text{A}$, $I_{B1} = 2.4\text{A}$ $f_H = 31.5\text{kHz}$

Main Characteristics





Package Dimensions (Unit: mm)

